Bipolar Transistor

DSAF00500L

Panasonic

DSAF00500L

Silicon PNP epitaxial planar type

For general amplification Complementary to DSCF005 DSA3005 in ML3 type package

■ Features

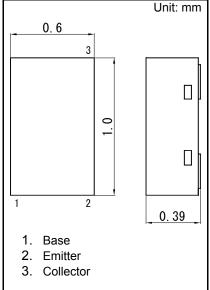
- · High forward current transfer ratio hFE with excellent linearity
- Low collector-emitter saturation voltage Vce(sat)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: A3

■ Packaging

Embossed type (Thermo-compression sealing): 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C Parameter Symbol Rating Unit Collector-base voltage (Emitter open) **VCBO** -60 V V Collector-emitter voltage (Base open) **VCEO** -50 V Emitter-base voltage (Collector open) **VEBO** -6 -200 Collector current IC mA Peak collector current ICp -300 mA Collector power dissipation Pc 100 mW 150 °C Junction temperature Τj Tstg -55 to +150 °C Storage temperature

Note) *1 : Copper plate at the collector is 5.0 mm 2 on substrate at 10 x 12 x 0.8t mm.



Panasonic	ML3-N4-B
JEITA	SC-101
Code	SOT-883

■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit		
Collector-emitter voltage (Base open)	VCEO	$IC = -100\mu A$, $IB = 0$	-50			V		
Collector-base cutoff current (Emitter open)	ICBO	VCB = -60 V, IE = 0			-0.1	μA		
Emitter-base cutoff current (Collector open)	IEBO	VEB = -6 V, IC = 0			-0.1	μA		
Forward current transfer ratio	hFE1	VCE = -6 V, IC = -1mA	150		390	-		
Forward current transfer ratio	hFE2	VCE = -6 V, IC = -0.1mA	90			-		
Collector-emitter saturation voltage	VCE(sat)	IC = -100 mA, IB = -10 mA			-0.3	V		
Transition frequency	fT	VCE = -6 V, IC = -10 mA		150		MHz		
Collector output capacitance (Common base, input open circuited)	Cob	VCB = -6 V, IE = 0, f = 1 MHz		5.0		pF		
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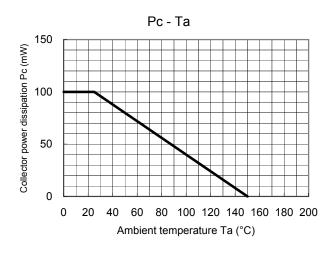
 $Note) \, 1. \quad \text{Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.}$

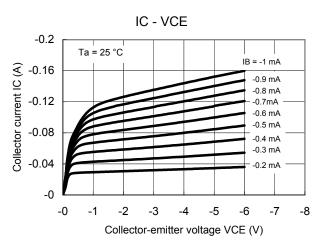
Revision . 2

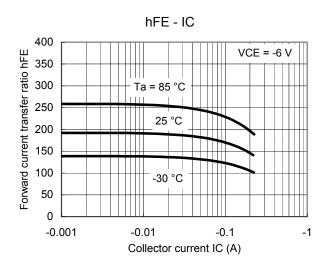
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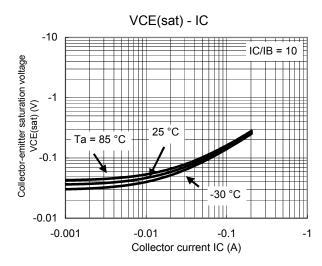
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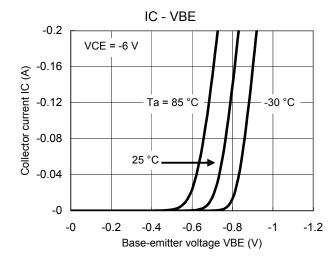
Technical Data (reference)

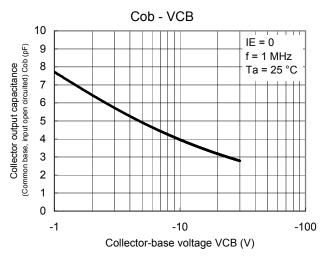












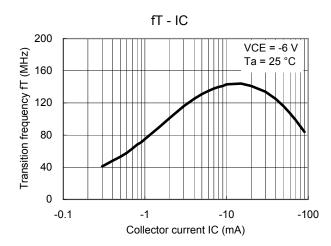
Established: 2012-03-06 Revised: 2012-12-25 Doc No. TT4-EA-14131 Revision . 2

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Bipolar Transistor DSAF00500L

Technical Data (reference)



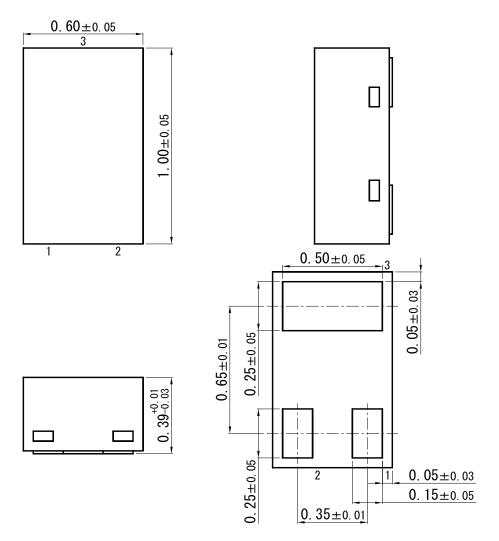
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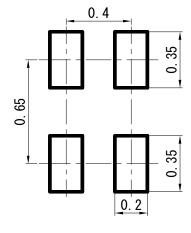
ML3-N4-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)

Established: 2012-03-06 Revised: 2012-12-25



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